

1.5mm Dia., TO-18 Package, InGaAs Photodiode



InGaAs Photodiodes (FC Receptacle , TO-5, TO-46)

Stock **#17-076** **3 In Stock**

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1

+

€301^{.00}

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Volume Pricing	
Qty 1-4	€301,00 each
Qty 5-9	€264,00 each
Qty 10+	€249,00 each
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 Prices shown are exclusive of VAT/local taxes

Product Downloads

SPECIFICATIONS

General

AR Coated Flat Window

Type of Optics:

InGaAs Photodiode	Type:
TO-18	Package:
Physical & Mechanical Properties	
1.5	Active Area Diameter (mm):
Optical Properties	
900 - 1700	Spectral Response (nm):
Electrical	
0.8 minimum / 0.9 typical	Responsivity @ 1310nm (A/W):
0.9 minimum / 0.95 typical	Responsivity @ 1550nm (A/W):
20	Shunt Resistance @ V=-10mV (MΩ):
200 typical / 450 maximum	Capacitance @ V _R =0V (pF):
3.01 x 10 ⁻¹⁴	Noise Equivalent Power NEP (W/ Hz ^{1/2}):
10	Maximum Forward Current (mA):
2	Maximum Reverse Current (mA):
2	Maximum Reverse Voltage (V):
Regulatory Compliance	
View	Certificate of Conformance:

PRODUCT DETAILS

- Response Range From 900nm to 1700nm
- Package Supports Single and Multi-Mode Fiber Coupling
- Both Small Area (High Speed) and Large Area
- [Segmented InGaAs Photodiodes](#) Also Available

InGaAs Photodiodes feature excellent responsivity from 900nm to 1700nm with active areas ranging from 0.07mm to 3.0mm. Photodiodes with active area sizes less than 1mm provide low capacitance, low dark current, and high responsivity from 1100nm to 1620nm, for high speed datacom and telecom applications. Photodiodes with active area sizes of 1mm and up provide large active areas, low noise, and high shunt resistance enabling high sensitivity for weak signals. InGaAs Photodiodes are isolated in TO-46, TO-18, or TO-5 packages with either a ball lens or double-sided AR coated window, depending on the packaging. These photodiodes are ideal for a multitude of research and OEM applications including IR laser alignment, medical diagnostics, and chemical analysis.

Note: To ensure well centered incident light, a [focusing lens](#) or [pinhole](#) is recommended due to inhomogeneity at the edge of the photodiode chip which can cause a decrease in detector responsivity.

TECHNICAL INFORMATION

